

T-33-31

PNP Transistor

6501130 NATL SEMICOND, (DISCRETE)

28C 35465 D



DARLINGTON

Type No.	Case Style	VCBO (V) Min	VCE [*] V _{CEO} (V) Min	VEBO (V) Min	I _{CE} [*] I _{CEXT} [†] (μA) Max	V _{CB} (V) e	h _{FE} Min Max	I _C (A) e V _{CE} (V)	V _{CE(SAT)} (V) Max	V _{BE(SAT)} (V) Min Max	I _C (A) e	C _{ob} (pF) Max	f _T (MHz) Min Max	I _C (A) e	Process No.
D41K1	TO-202 (55)		30*	13	0.5	30	10,000 1000	0.2 5 1.5 5	1.5	2.5	1.5		100	0.02	61
D41K2	TO-202 (55)		50*	13	0.5	50	10,000 1000	0.2 5 1.5 5	1.5	2.5	1.5		100	0.02	61
D41K3	TO-202 (55)		30*	13	0.5	30	10,000 1000	0.2 5 1.5 5	1.5	2.5	1		100	0.02	61
D41K4	TO-202 (55)		50*	13	0.5	50	10,000 1000	0.2 5 1.5 5	1.5	2.5	1		100	0.02	61
MPSA62	TO-92 (92)		20*		0.1	15	20,000	10 5	1.0		10			0.01	61
MPSA63	TO-92 (92)		30*		0.1	30	10,000 5000	100 5 10 5	1.5		100		125	0.01	61
MPSA64	TO-92 (92)		30*		0.1	30	20,000 10,000	100 5 10 5	1.5		100		125	0.01	61
MPSA65	TO-92 (92)		30*		0.1	30	50,000 20,000	0.01 5 0.1 5	1.5				100	0.01	61
MPSA66	TO-92 (92)		30*		0.1	30	75,000 40,000	0.01 5 0.1 5	1.5				100	0.01	61
NSDU95	TO-202 (55)	50		10			25,000 15,000 4000	0.2 5 0.5 5 1 5	1.5		1		50	0.02	61
NSDU95A	TO-202 (55)	60		10			25,000 15,000 4000	0.2 5 0.5 5 1 5	1.5		1		50	0.02	61
2N6034	TO-126		40		500	40	100 750 500	4 3 15,000 2 3	2.0		2	200	25	0.75	5J
2N6035	TO-126		60		500	60	100 750 500	4 3 15,000 2 3	2.0	4.0	2	200	25	0.75	5J
2N6036	TO-126		80		500	80	100 750 500	4 3 15,000 2 3	2.0	4.0	2	200	25	0.75	5J
2N6040	TO-220		60		500†	60	100 750 500	4 3 15,000 2 3	2.0		4	300			5J
2N6041	TO-220		80		500†	80	100 750 500	4 3 15,000 2 3	2.0		4	300			5J
MJE700	TO-126		60		200	60	750	1.5 3	2.5		1.5		1	1.5	5J
MJE701	TO-126		60		200	60	750	2 3 2.8	2.5		2		1	1.5	5J
MJE702	TO-126		80		200	80	750	1.5 3	2.5		1.5		1	1.5	5J
MJE703	TO-126		80		200	80	750	2 3	2.8		2		1	1.5	5J

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DARLINGTON (Continued)

Type No.	Case Style	V _{CEO} (V) Min	V _{CE0} (V) Min	V _{BE0} (V) Min	ICES* (μA) Max	V _{CB} (V) @ I _C	h _{FE} Min	h _{FE} Max	I _C (A) @ V _{CE}	V _{CE(SAT)} (V) Max	V _{BE(SAT)} (V) Min	I _C (A) @ V _{BE(SAT)}	C _{ob} (pF) Max	f _T (MHz) Min	f _T (MHz) Max	IC (A)	Process No.
TIP115	TO-220	60	60	60	1 mA	60	500	1000	2	2.5		2					5J
TIP116	TO-220	80	80	80	1 mA	80	500	1000	2	2.5		2					5J
TIP117	TO-220	100	100	100	1 mA	100	500	1000	2	2.5		2					5J
TIP125	TO-220	60	60	60	200	60	1000	1000	3	4.0		5					5J
TIP126	TO-220	80	80	80	200	80	1000	1000	3	4.0		5					5J
TIP127	TO-220	100	100	100	200	100	1000	1000	3	4.0		5					5J
2N6042	TO-220	100	100	100	500†	100	1000	20,000	4	2.0		4	300				5K
SE9400	TO-220	60	60	60			750	1000	1	2.0		4					5K
SE9401	TO-220	80	80	80			1000	1000	4	2.5		7.5		1			5K
SE9402	TO-220	100	100	100			1000	1000	7.5	2.0		4		1			5K
TIP105	TO-220	60	60	60			1000	20,000	3	2.5		7.5					5K
TIP106	TO-220	80	80	80			1000	20,000	3	2.5		8					5K
TIP107	TO-220	100	100	100			1000	20,000	3	2.5		8					5K
TIP135	TO-220	60	60	60	200	60	1000	15,000	4	3.0		6	200				5K
TIP136	TO-220	80	80	80	200	80	1000	15,000	4	3.0		6	200				5K
TIP137	TO-220	100	100	100	200	100	1000	15,000	4	3.0		6	200				5K

NP Transistors

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